MOS FET

SK8603140L

Panasonic

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Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : RDS(on) typ = 1.8 m Ω (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : 14

■ Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter			Rating		Unit		
Drain to Source Voltage			30		V		
Gate to Source Voltage			±	20	V		
Ta = 25 °C, t = 10 s *1			4	6			
Ta = 25 °C, DC *1		ID	2	5	Α		
Tc = 2	Γc = 25 °C		1	03	^		
Pulsed	I, Tch < 150 °C ^{*2}		1:	38	' 		
Total Power Ta = 25 °C, DC *1		DD	2	W			
Dissipation		Pυ	4	.0	VV		
I nermai Resistance ———		Rth(ch-a)	50		°C / W		
		Rth(ch-c)	3.1		-0/00		
Channel Temperature			150				
Operating ambient temperature		Topr	-40 to	+85	°C		
Storage Temperature Range		Tstg	-55 to	+150			
Avalanche Current (Single pulse) *3		IAR	23		Α		
Avalanche Energy (Single pulse) *3		EAR	61		mJ		
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Voltag /oltag /oltag /a = 2 /a = 2 /c = 2 /ulsec nce rature rature ature ent (Si	Voltage /oltage Ta = 25 °C, t = 10 s *1 Ta = 25 °C, DC *1 Tc = 25 °C Pulsed, Tch < 150 °C *2 Ta = 25 °C, DC *1 Tc = 25 °C Channel to Ambient Channel to Case rature Int temperature atture Range Int (Single pulse) *3	Voltage VDS Voltage VGS Ta = 25 °C, t = 10 s *1 Ta = 25 °C, DC *1 Tc = 25 °C Pulsed, Tch < 150 °C *2 Ta = 25 °C, DC *1 Tc = 25 °C Channel to Ambient Rth(ch-a) Channel to Case Rth(ch-c) Tature Tch Tch Tature Range Tstg Ent (Single pulse) *3 INS VDS VDS VDS VDS VDS VDS VDS V	Voltage VDS 3 /oltage VGS ±2 Ta = 25 °C, t = 10 s *1 4 4 Ta = 25 °C, DC *1 2 10 Pulsed, Tch < 150 °C *2	Voltage VDS 30 /oltage VGS ±20 Ta = 25 °C, t = 10 s *1 46 Ta = 25 °C, DC *1 25 Tc = 25 °C 103 Pulsed, Tch < 150 °C *2		

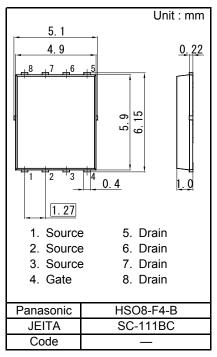
Note *1 Device mounted on a glass-epoxy board in Figure 1

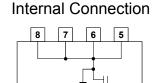
Established: 2012-12-10

: 2013-05-31

Revised

- *2 Pulse test: Ensure that the channel temperature does not exceed 150 °C
- *3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 $^{\circ}$ C (initial)





2

Pin Name

- 5. Drain 1. Source
- 2. Source 6. Drain
- 3. Source 7. Drain 4. Gate 8. Drain



Figure 1 FR4 Glass-Epoxy Board 25.4 mm × 25.4 mm × 0.8 mm

Doc No. TT4-EA-14461 Revision. 3

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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ± 16 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	_	ID = 5.85 mA, VDS = 10 V	1.3		3	V
		ID = 23 A, VGS = 10 V		1.6	2.2	mΩ
	RDS(on)2	ID = 23 A, VGS = 4.5 V		1.8	2.5	

Dynamic Characteristics

Byttattile Characteriotics						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		4 900	6 860	
Output Capacitance	Coss			570	798	pF
Reverse Transfer Capacitance	Crss			410	656	
Turn-on Delay Time *1	td(on)	VDD = 15 V, VGS = 0 to 10 V ID = 23 A		18		ns
Rise Time *1	tr			14		115
Turn-off Delay Time *1	td(off)	VDD = 15 V, VGS = 10 to 0 V ID = 23 A		75		no
Fall Time *1	tf			11		ns
Total Gate Charge	Qg	VDD = 15 V VCC = 0 to 4 5 V		37		
Gate to Source Charge	Qgs	VDD = 15 V, VGS = 0 to 4.5 V ID = 23 A		12		nC
Gate to Drain Charge	Qgd	ID = 23 A		14		
Gate resistance	rg	f = 5 MHz		1.2	3	Ω

Body Diode Characteristic

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 23 A, VGS = 0 V		0.8	1.2	V

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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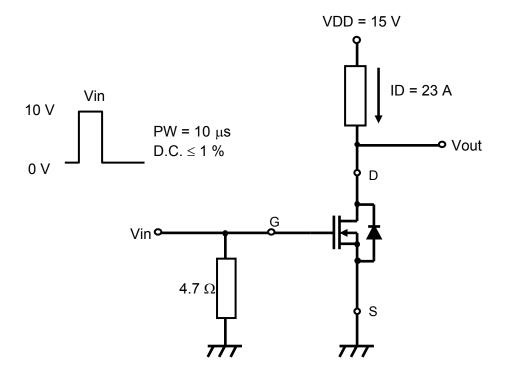
^{2. *1} Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

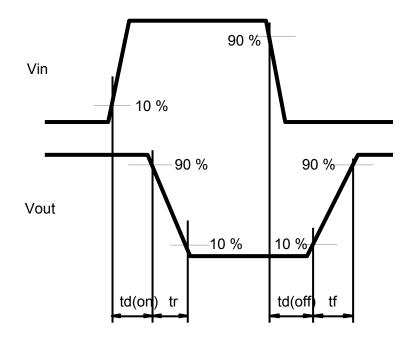
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*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



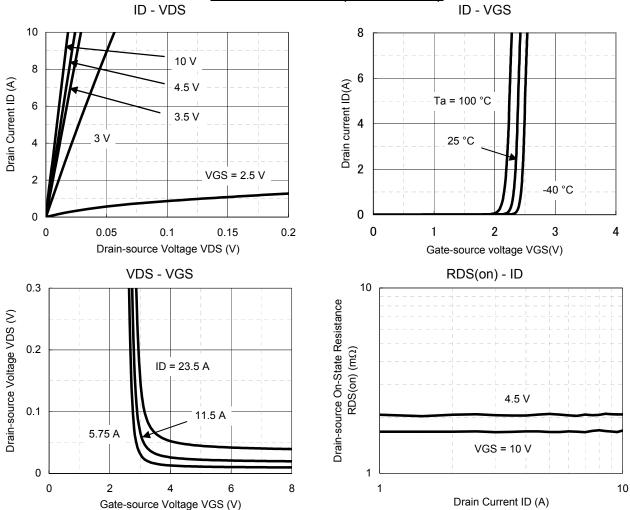


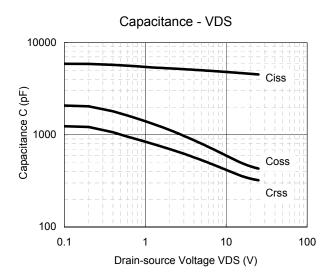
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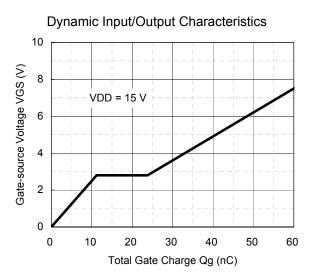
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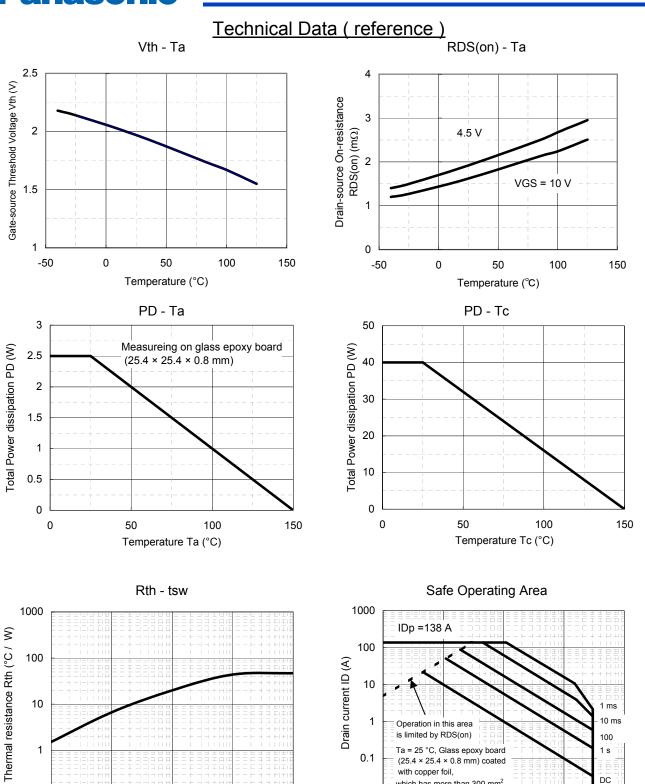




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100

10

which has more than 300 mm²

Drain-source Voltage VDS (V)

0.1

0.01

0.01

Established: 2012-12-10 Revised

0.1

0.1

10

Pulse Width tsw (s)

100

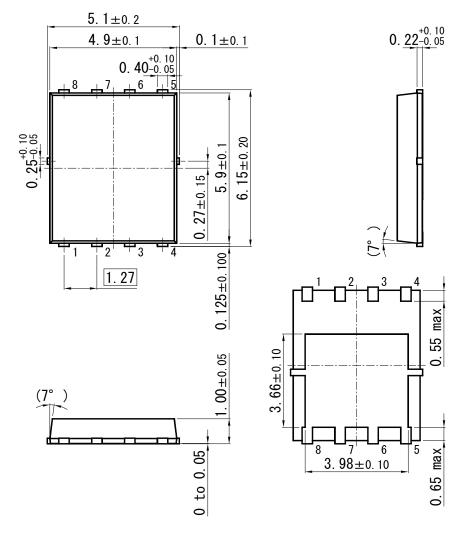
1000

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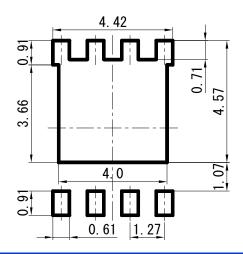
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HSO8-F4-B



■ Land Pattern (Reference) (Unit : mm)



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